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**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2kV HBM

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V	
$V_{GS}$	gate-source voltage			-20	-	20	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	350	mA	
Static charac	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 200 mA; $T_j$ = 25 °C		-	2.2	2.8	Ω	

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.





60 V, N-channel Trench MOSFET

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	2 3	
3	D	drain	Transparent top view  DFN1006B-3 (SOT883B)	G S 017aaa255

# 6. Ordering information

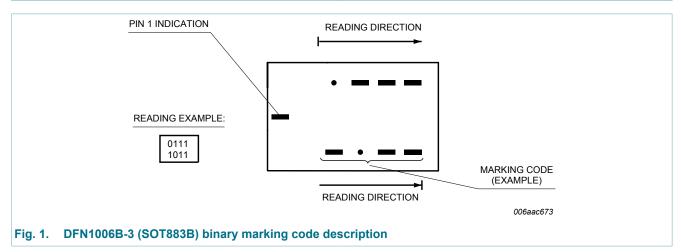
Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX7002BKMB	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
NX7002BKMB	0101 0111



60 V, N-channel Trench MOSFET

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	350	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	200	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	0.9	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	<u>[2]</u>	-	350	mW
			[1]	-	680	mW
		T <sub>sp</sub> = 25 °C		-	3100	mW
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain o	liode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	200	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

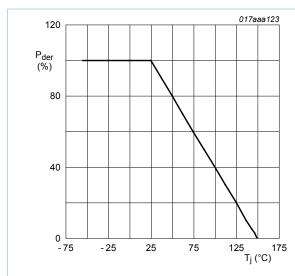


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

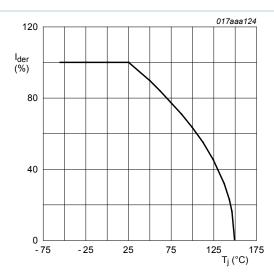


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

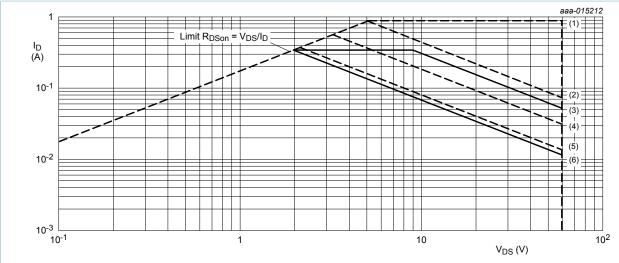
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3 / 16

### 60 V, N-channel Trench MOSFET



I<sub>DM</sub> = single pulse

(1) 
$$t_p = 10 \mu s$$

(2) 
$$t_p = 1 \text{ ms}$$

(3) DC; 
$$T_{sp} = 25 \,^{\circ}\text{C}$$

$$(4) t_p = 10 ms$$

$$(5) t_p = 100 \text{ ms}$$

(6) DC;  $T_{amb}$  = 25 °C; drain mounting pad 1 cm<sup>2</sup>

Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	314	360	K/W
			[2]	-	159	180	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	35	40	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

### 60 V, N-channel Trench MOSFET

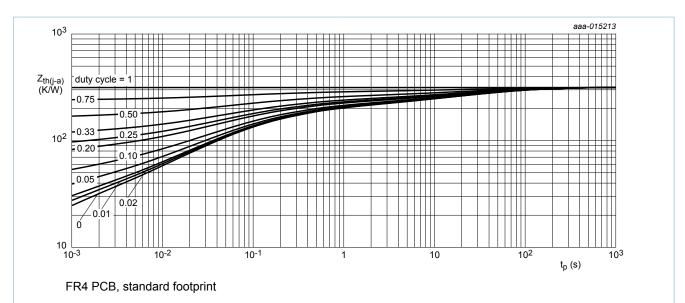


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

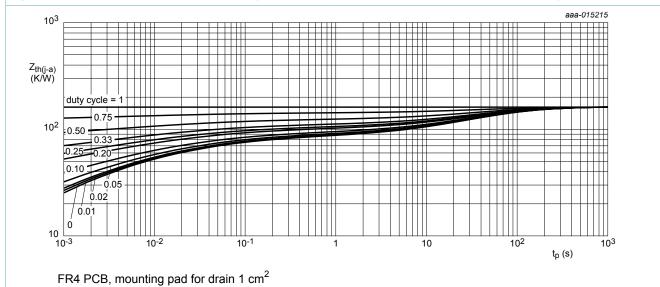


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

**60 V, N-channel Trench MOSFET** 

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			,		
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
		V <sub>GS</sub> = 5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.3	μΑ
		V <sub>GS</sub> = -5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.3	μA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	2.2	2.8	Ω
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 150 °C	-	4.5	5.7	Ω
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	2.5	3.2	Ω
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	600	-	mS
$R_G$	internal gate resistance (AC)	f = 2.5 MHz	-	2.5	-	Ω
Dynamic ch	naracteristics		1			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V;	-	1	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.18	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	23.6	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	4.6	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; $I_{D}$ = 200 mA; $V_{GS}$ = 10 V;	-	4.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4.3	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	6.9	-	ns
t <sub>f</sub>	fall time		-	2.9	-	ns
Source-dra	in diode		I	1	-1	
V <sub>SD</sub>	source-drain voltage	$I_S$ = 200 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.87	1.2	V

### **60 V, N-channel Trench MOSFET**

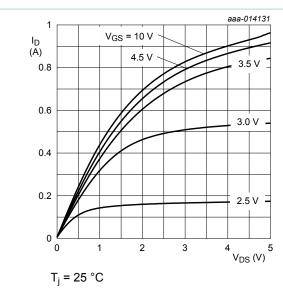


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

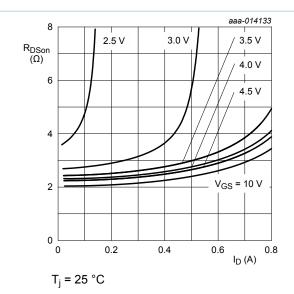
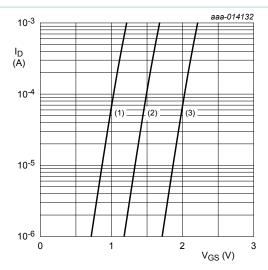


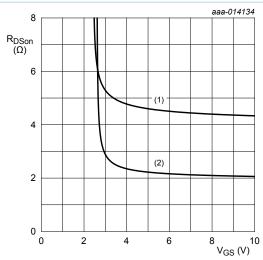
Fig. 9. Drain-source on-state resistance as a function of drain current; typical values



 $T_j$  = 25 °C;  $V_{DS}$  = 5 V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage



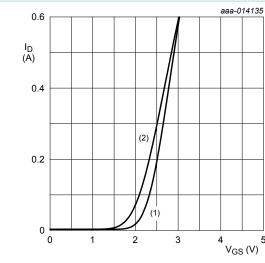
 $I_D = 0.2 A$ 

(1)  $T_i = 150 \,^{\circ}C$ 

(2)  $T_i = 25 \,^{\circ}C$ 

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

### 60 V, N-channel Trench MOSFET



 $V_{DS} > I_{D} \times R_{DSon}$ 

(1)  $T_j = 25 \, ^{\circ}C$ 

(2)  $T_j = 150 \, ^{\circ}C$ 

Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

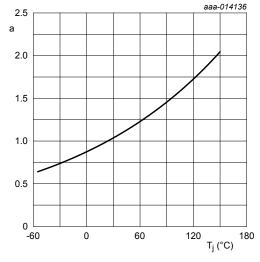
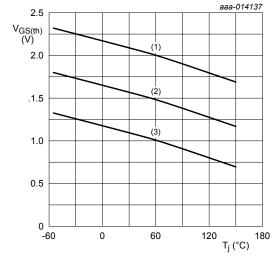


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

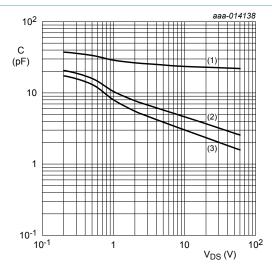
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3)  $C_{rss}$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 60 V, N-channel Trench MOSFET

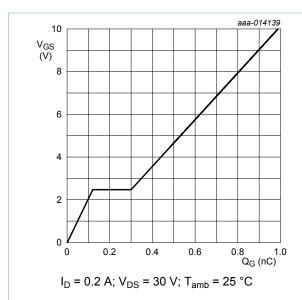


Fig. 15. Gate-source voltage as a function of gate charge; typical values

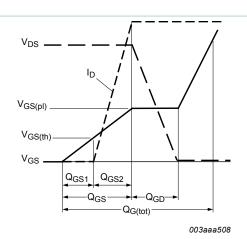
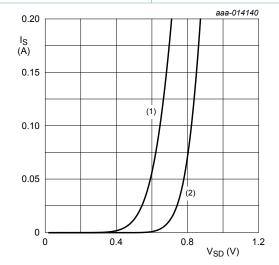


Fig. 16. MOSFET transistor: Gate charge waveform definitions



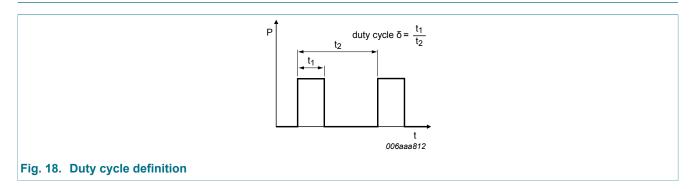
 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 17. Source current as a function of source-drain voltage; typical values

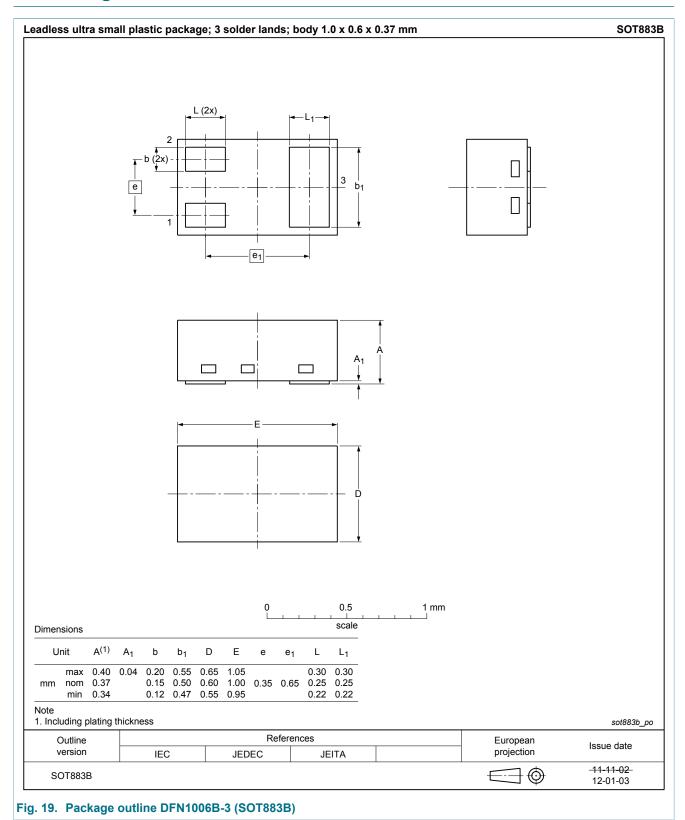
**60 V, N-channel Trench MOSFET** 

# 11. Test information



60 V, N-channel Trench MOSFET

## 12. Package outline



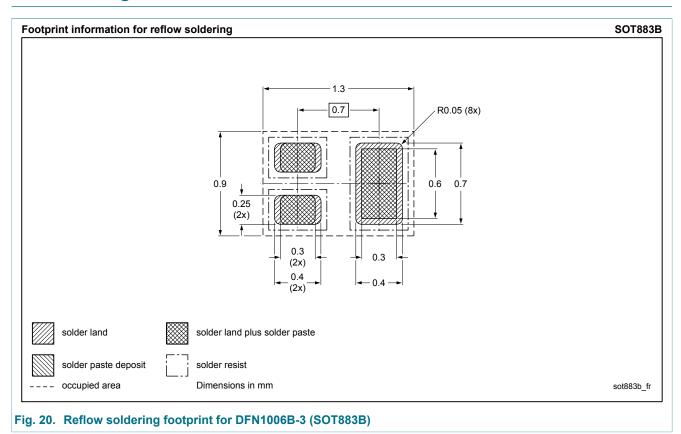
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60 V, N-channel Trench MOSFET

## 13. Soldering



**60 V, N-channel Trench MOSFET** 

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX7002BKMB v.2	20141203	Product data sheet	-	NX7002BKMB v.1
Modification:	Figure 3 updated			
NX7002BKMB v.1	20141001	Product data sheet	-	-

#### 60 V, N-channel Trench MOSFET

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#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### **60 V, N-channel Trench MOSFET**

### 16. Contents

General description	1
Features and benefits	1
Applications	1
Quick reference data	1
Pinning information	2
Ordering information	2
Marking	2
Limiting values	3
Thermal characteristics	4
Characteristics	6
Test information	10
Package outline	11
Soldering	12
Revision history	13
Legal information	14
Data sheet status	14
Definitions	14
Disclaimers	14
Trademarks	15
	General description Features and benefits Applications Quick reference data Pinning information Ordering information Marking Limiting values Thermal characteristics Characteristics Test information Package outline Soldering Revision history Legal information Data sheet status Definitions Disclaimers Trademarks

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